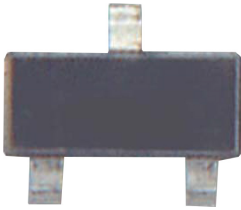
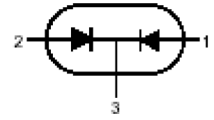


# Low Power Signal Diode



## Features:

- Silicon planar epitaxial high-speed diode
- Supplied on 8mm tape



Pin Configuration

1 = Anode

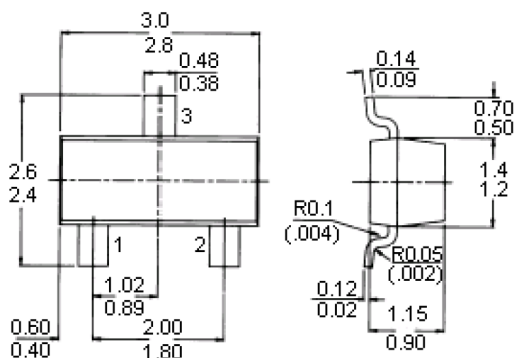
2 = Anode

3 = Cathode

## Absolute Maximum Ratings:

Description	Symbol		Values	Unit
Continuous reverse voltage	$V_R$	Maximum	70	V
Repetitive peak reverse voltage	$V_{RRM}$		75	
Repetitive peak forward current	$I_{FRM}$		450	mA
Junction temperature	$T_j$		150	°C
Forward voltage $I_F = 50\text{mA}$	$V_F$	<	1	V
Reverse recovery time when switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$ ; $R_L = 100\Omega$ ; measured at $I_R = 1\text{mA}$	$t_{rr}$	<	4	ns
Recovery charge when switched from $I_F = 10\text{mA}$ to $V_R = 5\text{V}$ ; $R_L = 100\Omega$	$Q_s$	<	45	pc
Continuous reverse voltage	$V_R$	Maximum	70	V
Repetitive peak reverse voltage	$V_{RRM}$		75	
Forward current (DC)	$I_F$		215	mA
Repetitive peak forward current	$I_{FRM}$		450	
Non-repetitive peak forward current (per crystal) $t = 1\text{nS}$ $t = 1\text{mS}$ $t = \text{s}$	$I_{FSM}$ $I_{FSM}$ $I_{FSM}$		4 1 0.5	
Storage temperature range	$T_{STG}$	-55 to +150		°C
Junction temperature	$T_j$	Maximum	150	
From junction to ambient $T_j = 25\text{ °C}$ unless otherwise specified	$R_{th(j-a)}$	=	500	K/W
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 50\text{ mA}$ $I_F = 150\text{ mA}$	$V_F$ $V_F$ $V_F$ $V_F$	< < < <	715 855 1,000 1,250	mV
Reverse current $V_R = 25\text{V}$ ; $T_j = 150\text{ °C}$ $V_R = 70\text{V}$ $V_R = 70\text{V}$ ; $T_j = 150\text{ °C}$	$I_R$ $I_R$ $I_R$	< < <	60 2.5 100	mA
Diode capacitance $V_R = 0$ ; $f = 1\text{MHz}$	$C_d$	<	1.5	pF
Forward recovery voltage when switched to $I_F = 10\text{mA}$ , $t_r = 20\text{ns}$	$V_{fr}$	<	1.75	V

# Low Power Signal Diode



Height	Width	Depth
1.12mm	3.05mm	2.5mm

Dimensions : Millimetres

## Part Number Table

Description	Connection	V <sub>RRM</sub> Max (V)	I <sub>F</sub> Max (mA)	V <sub>F</sub> Max. (V) at I <sub>F</sub> = 10mA	Device Marking	Package	Part Number
Diode, Dual, SOT-23	Dual Diode	70	200	1	A4	SOT - 23	TBAV70

**Important Notice** : This data sheet and its contents (the "Information") belong to the members of the Premier Farnell group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp is the registered trademark of the Group. © Premier Farnell plc 2012.

www.element14.com  
www.farnell.com  
www.newark.com

